

# P2N2222A

## Amplifier Transistors

### NPN Silicon

#### Features

- These are Pb-Free Devices\*

#### MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Value	Unit
Collector – Emitter Voltage	$V_{CEO}$	40	Vdc
Collector – Base Voltage	$V_{CBO}$	75	Vdc
Emitter – Base Voltage	$V_{EBO}$	6.0	Vdc
Collector Current – Continuous	$I_C$	600	mA dc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	1.5 12	W mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	$^\circ\text{C/W}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



ON Semiconductor®

<http://onsemi.com>



TO-92  
CASE 29  
STYLE 17



STRAIGHT LEAD  
BULK PACK



BENT LEAD  
TAPE & REEL  
AMMO PACK

#### MARKING DIAGRAM



A = Assembly Location

Y = Year

WW = Work Week

▪ = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

Device	Package	Shipping†
P2N2222AG	TO-92 (Pb-Free)	5000 Units/Bulk
P2N2222ARL1G	TO-92 (Pb-Free)	2000/Tape & Ammo

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# P2N2222A

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector – Emitter Breakdown Voltage ( $I_C = 10\text{ mA}$ , $I_B = 0$ )	$V_{(BR)CEO}$	40	–	Vdc
Collector – Base Breakdown Voltage ( $I_C = 10\text{ }\mu\text{A}$ , $I_E = 0$ )	$V_{(BR)CBO}$	75	–	Vdc
Emitter – Base Breakdown Voltage ( $I_E = 10\text{ }\mu\text{A}$ , $I_C = 0$ )	$V_{(BR)EBO}$	6.0	–	Vdc
Collector Cutoff Current ( $V_{CE} = 60\text{ Vdc}$ , $V_{EB(off)} = 3.0\text{ Vdc}$ )	$I_{CEX}$	–	10	nAdc
Collector Cutoff Current ( $V_{CB} = 60\text{ Vdc}$ , $I_E = 0$ ) ( $V_{CB} = 60\text{ Vdc}$ , $I_E = 0$ , $T_A = 150^\circ\text{C}$ )	$I_{CBO}$	– –	0.01 10	$\mu\text{Adc}$
Emitter Cutoff Current ( $V_{EB} = 3.0\text{ Vdc}$ , $I_C = 0$ )	$I_{EBO}$	–	10	nAdc
Collector Cutoff Current ( $V_{CE} = 10\text{ V}$ )	$I_{CEO}$	–	10	nAdc
Base Cutoff Current ( $V_{CE} = 60\text{ Vdc}$ , $V_{EB(off)} = 3.0\text{ Vdc}$ )	$I_{BEX}$	–	20	nAdc

## ON CHARACTERISTICS

DC Current Gain ( $I_C = 0.1\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ ) ( $I_C = 1.0\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ ) ( $I_C = 10\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ ) ( $I_C = 10\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ , $T_A = -55^\circ\text{C}$ ) ( $I_C = 150\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ ) (Note 1) ( $I_C = 150\text{ mA}$ , $V_{CE} = 1.0\text{ Vdc}$ ) (Note 1) ( $I_C = 500\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ ) (Note 1)	$h_{FE}$	35 50 75 35 100 50 40	– – – – 300 – –	–
Collector – Emitter Saturation Voltage (Note 1) ( $I_C = 150\text{ mA}$ , $I_B = 15\text{ mA}$ ) ( $I_C = 500\text{ mA}$ , $I_B = 50\text{ mA}$ )	$V_{CE(sat)}$	– –	0.3 1.0	Vdc
Base – Emitter Saturation Voltage (Note 1) ( $I_C = 150\text{ mA}$ , $I_B = 15\text{ mA}$ ) ( $I_C = 500\text{ mA}$ , $I_B = 50\text{ mA}$ )	$V_{BE(sat)}$	0.6 –	1.2 2.0	Vdc

## SMALL-SIGNAL CHARACTERISTICS

Current – Gain – Bandwidth Product (Note 2) ( $I_C = 20\text{ mA}$ , $V_{CE} = 20\text{ Vdc}$ , $f = 100\text{ MHz}$ )C	$f_T$	300	–	MHz
Output Capacitance ( $V_{CB} = 10\text{ Vdc}$ , $I_E = 0$ , $f = 1.0\text{ MHz}$ )	$C_{obo}$	–	8.0	pF
Input Capacitance ( $V_{EB} = 0.5\text{ Vdc}$ , $I_C = 0$ , $f = 1.0\text{ MHz}$ )	$C_{ibo}$	–	25	pF
Input Impedance ( $I_C = 1.0\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ ) ( $I_C = 10\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ )	$h_{ie}$	2.0 0.25	8.0 1.25	k $\Omega$
Voltage Feedback Ratio ( $I_C = 1.0\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ ) ( $I_C = 10\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ )	$h_{re}$	– –	8.0 4.0	$\times 10^{-4}$
Small-Signal Current Gain ( $I_C = 1.0\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ ) ( $I_C = 10\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ )	$h_{fe}$	50 75	300 375	–
Output Admittance ( $I_C = 1.0\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ ) ( $I_C = 10\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ )	$h_{oe}$	5.0 25	35 200	$\mu\text{Mhos}$
Collector Base Time Constant ( $I_E = 20\text{ mA}$ , $V_{CB} = 20\text{ Vdc}$ , $f = 31.8\text{ MHz}$ )	$r_b'C_c$	–	150	ps
Noise Figure ( $I_C = 100\text{ }\mu\text{A}$ , $V_{CE} = 10\text{ Vdc}$ , $R_S = 1.0\text{ k}\Omega$ , $f = 1.0\text{ kHz}$ )	$N_F$	–	4.0	dB

1. Pulse Test: Pulse Width  $\leq 300\text{ }\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .
2.  $f_T$  is defined as the frequency at which  $|h_{fe}|$  extrapolates to unity.

# P2N2222A

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
<b>SWITCHING CHARACTERISTICS</b>				
Delay Time	$t_d$	—	10	ns
Rise Time	$t_r$	—	25	ns
Storage Time	$t_s$	—	225	ns
Fall Time	$t_f$	—	60	ns

## SWITCHING TIME EQUIVALENT TEST CIRCUITS



Figure 1. Turn-On Time



Figure 2. Turn-Off Time



Figure 3. DC Current Gain

# P2N2222A

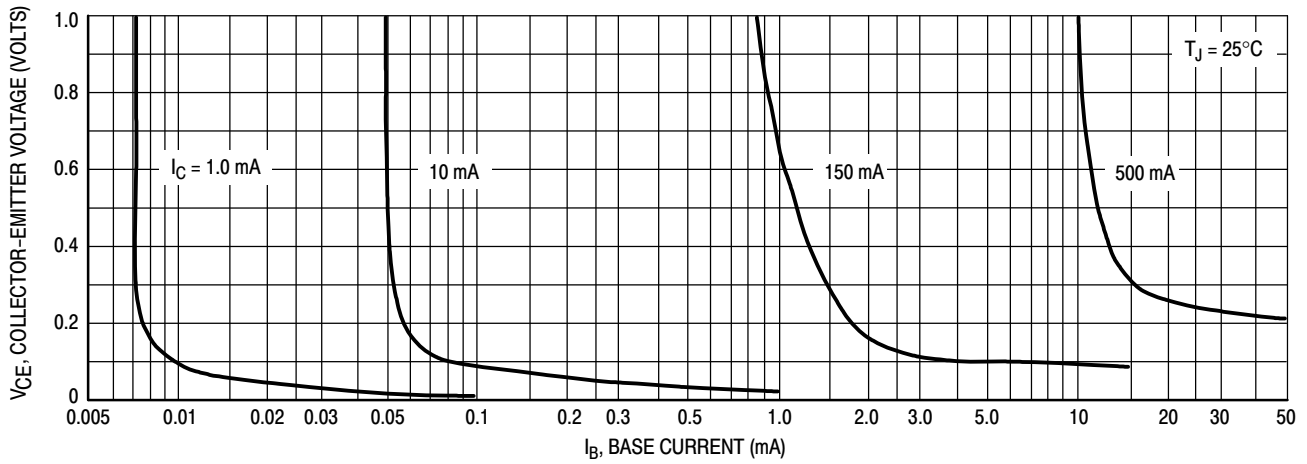




Figure 9. Capacitances



Figure 10. Current-Gain Bandwidth Product



Figure 11. "On" Voltages



Figure 12. Temperature Coefficients